

STGB10NB60S STGP10NB60S

16 A, 600 V, low drop IGBT

Features

- Low on-voltage drop (V_{CE(sat)})
- High current capability

Applications

- Light dimmer
- Static relays
- Motor drive

Description

This IGBT utilizes the advanced PowerMESH[™] process featuring extremely low on-state voltage drop in low-frequency working conditions (up to 1 kHz).

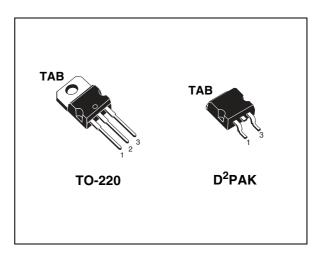


Figure 1. Internal schematic diagram

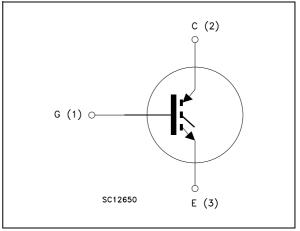


Table 1. Device summary

Order codes	Marking	Package	Packaging
STGB10NB60ST4	GB10NB60S	D ² PAK	Tape and reel
STGP10NB60S	GP10NB60S	TO-220	Tube

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1 Electrical ratings

Table 2.	Absolute	maximum	ratings
	Absolute	maximum	ratings

Symbol	Parameter	Value	Unit
V _{CES}	Collector-emitter voltage (V _{GE} = 0)	600	V
I _C ⁽¹⁾	Continuous collector current at $T_{C} = 25 \ ^{\circ}C$	29	A
I _C ⁽¹⁾	Continuous collector current at $T_{C} = 100 \ ^{\circ}C$	16	А
I _{CL} ⁽²⁾	Turn-off latching current	20	А
I _{CP} ⁽³⁾	Pulsed collector current	80	А
V _{GE}	Gate-emitter voltage	± 20	V
P _{TOT}	Total dissipation at T_{C} = 25 °C	80	W
Т _ј	Operating junction temperature	– 55 to 150	°C

1. Calculated according to the iterative formula

$$I_{C}(T_{C}) = \frac{T_{j(max)} - T_{C}}{R_{thj-c} \times V_{CE(sat)(max)}(T_{j(max)}, I_{C}(T_{C}))}$$

2. Vclamp = 80% of V_{CES}, T_j =150 °C, R_G=1k $\Omega,$ V_GE=15 V

3. Pulse width limited by maximum junction temperature and turn-off within RBSOA

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction-case	1.56	°C/W
R _{thj-amb}	Thermal resistance junction-ambient	62.5	°C/W



2 Electrical characteristics

(T_j =25 °C unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)CES}	Collector-emitter breakdown voltage (V_{GE} = 0)	I _C = 250 μA	600			V
V _{(BR)ECS}	Emitter-collector breakdown voltage (V _{GE} = 0)	I _C = 1 mA	20			V
I _{GES}	Gate-emitter leakage current (V _{CE} = 0)	V _{GE} = ±20 V			±100	nA
I _{CES}	Collector cut-off current (V _{GE} = 0)	V _{CE} = 600 V V _{CE} = 600 V, T _j = 125 °C			10 100	μΑ μΑ
V _{GE(th)}	Gate threshold voltage	V_{CE} = V_{GE} , I_C = 250 μ A	2.5		5	V
V _{CE(sat)}	Collector-emitter saturation voltage	V_{GE} = 15 V, I _C = 5 A V_{GE} = 15 V, I _C = 10 A V_{GE} = 15 V, I _C = 10 A, T_{j} = 125 °C		1.15 1.35 1.25	1.75	V
9 _{fs} ⁽¹⁾	Forward transconductance	$V_{CE} = 15 V_{,I_{C}} = 10 A$	5			S

1. Pulsed: Pulse duration = 300 μ s, duty cycle 1.5%

Table 5.	Dynamic
	Dynamio

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
C _{ies} C _{oes} C _{res}	Input capacitance Output capacitance Reverse transfer capacitance	V _{CE} = 25 V, f = 1 MHz, V _{GE} = 0	-	610 65 12	-	pF pF pF
Qg	Total gate charge	$V_{CE} = 400 \text{ V}, I_C = 10 \text{ A},$ $V_{GE} = 15 \text{ V}$ (see Figure 17)	-	33	-	nC



	officinity official (inductive fead)					
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)} t _r (di/dt) _{on}	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 480 \text{ V}, \text{ I}_{C} = 10 \text{ A}$ $R_{G}=1 \text{ k}\Omega, \text{ V}_{GE}=15 \text{ V}$ (see Figure 16)	-	0.7 0.46 8	-	μs μs A/μs
t _r (V _{off}) t _d (_{off}) t _f	Off voltage rise time Turn-off delay time Current fall time	$V_{CC} = 480 \text{ V}, \text{ I}_{C} = 10 \text{ A}$ $R_{G}= 1 \text{ k}\Omega, \text{ V}_{GE}= 15 \text{ V}$ (see Figure 16)	-	2.2 1.2 1.2	-	μs
t _r (V _{off}) t _{d(off}) t _f	Off voltage rise time Turn-off delay time Current fall time	$V_{CC} = 480 \text{ V}, I_C = 10 \text{ A}$ $R_G = 1 \text{ k}\Omega, V_{GE} = 15 \text{ V},$ $T_j = 125 \text{ °C}$ <i>(see Figure 16)</i>	-	3.8 1.2 1.9	-	μs

Table 6. Switching on/off (inductive load)

Table 7. Switching energy (inductive load)

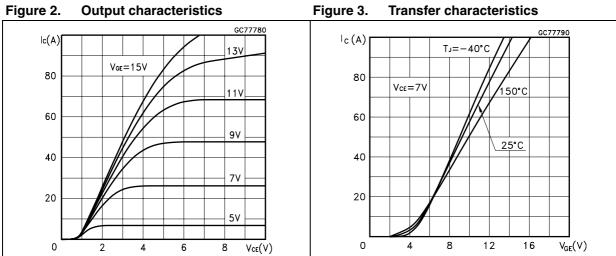
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
Eon ⁽¹⁾ E _{off} ⁽²⁾ E _{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	$V_{CC} = 480 \text{ V}, I_{C} = 10 \text{ A}$ $R_{G} = 1 \text{ k}\Omega, V_{GE} = 15 \text{ V}$ <i>(see Figure 16)</i>	-	0.6 5 5.6	-	mJ mJ mJ
E _{off} ⁽²⁾	Turn-off switching losses	$V_{CC} = 480 \text{ V}, I_C = 10 \text{ A}$ $R_G = 1 \text{ k}\Omega, V_{GE} = 15 \text{ V},$ $T_j = 125 \text{ °C}$ <i>(see Figure 16)</i>	-	8	-	mJ

 Eon is the turn-on losses when a typical diode is used in the test circuit. If the IGBT is offered in a package with a co-pack diode, the co-pack diode is used as external diode. IGBTs and diode are at the same temperature (25°C and 125°C).

2. Turn-off losses include also the tail of the collector current.



2.1 Electrical characteristics (curves)





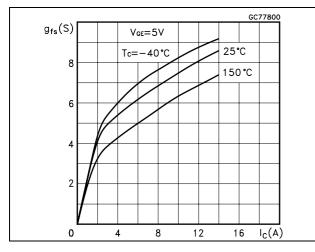
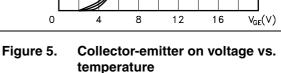
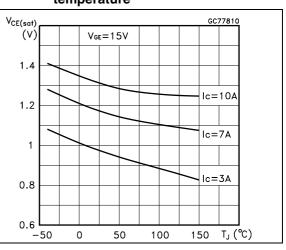


Figure 6. Collector-emitter on voltage vs. collector current





Normalized gate threshold vs. temperature

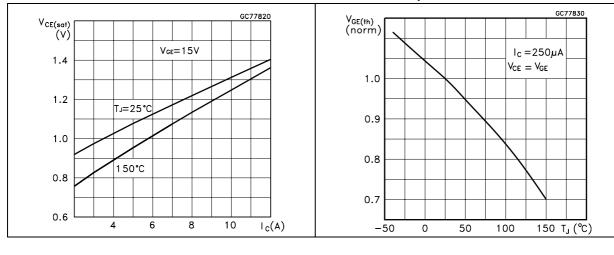


Figure 7.

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V_{CE} = 480V $I_{C} = 10A$

20

Switching losses vs. temperature

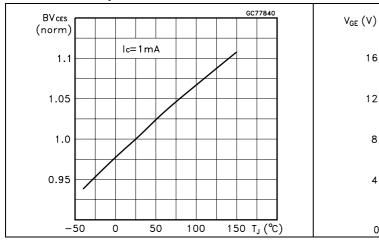
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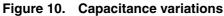
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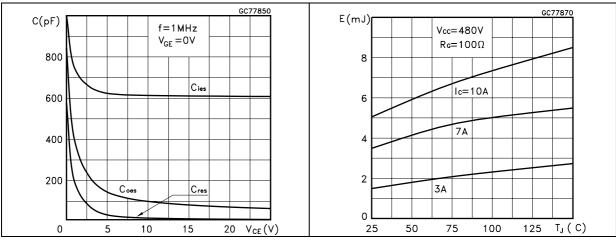
GC77860

 $Q_g(nC)$

Figure 8. Normalized breakdown voltage vs. Figure 9. Gate charge vs. gate-emitter temperature voltage







8

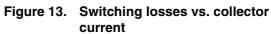
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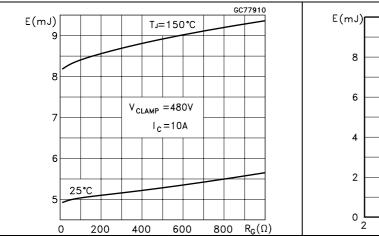
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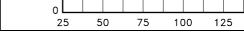
Figure 11.

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Figure 12. Switching losses vs. gate resistance







GC77890 Vcc=480V Rc=100Ω T_=150℃

6

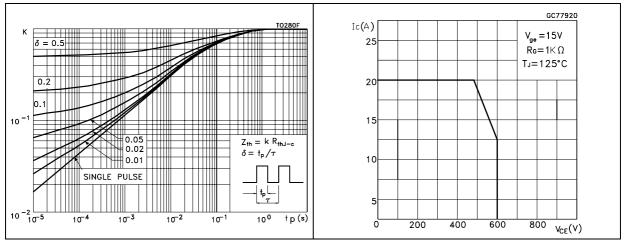
8

10

 $I_{c}(A)$

4

Figure 14. Thermal impedance for TO-220 and Figure 15. Turn-off SOA D²PAK





3 Test circuits

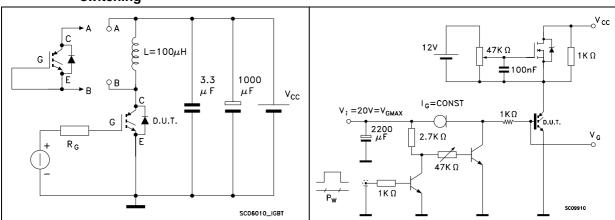
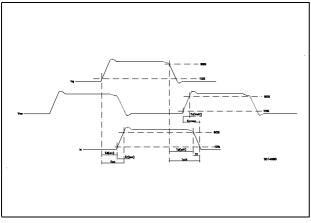


Figure 17. Gate charge test circuit

Figure 16. Test circuit for inductive load switching

Figure 18. Switching waveforms





4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.



Dim	mm			
Dim. —	Min.	Тур.	Max.	
A	4.40		4.60	
A1	0.03		0.23	
b	0.70		0.93	
b2	1.14		1.70	
С	0.45		0.60	
c2	1.23		1.36	
D	8.95		9.35	
D1	7.50			
E	10		10.40	
E1	8.50			
е		2.54		
e1	4.88		5.28	
н	15		15.85	
J1	2.49		2.69	
L	2.29		2.79	
L1	1.27		1.40	
L2	1.30		1.75	
R		0.4		
V2	0°		8 °	

 Table 8.
 D²PAK (TO-263) mechanical data





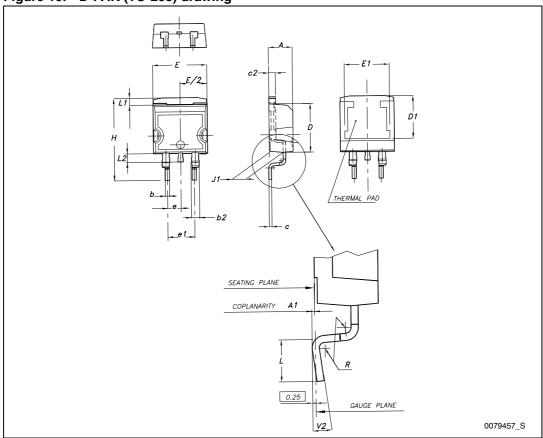
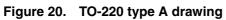
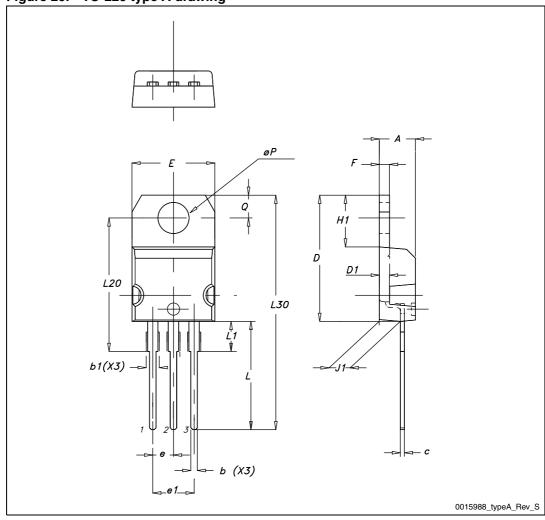


Table 9. TO-220 type A mechanical d	lata
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Dim.	mm.			
	Min.	Тур.	Max.	
А	4.40		4.60	
b	0.61		0.88	
b1	1.14		1.70	
с	0.48		0.70	
D	15.25		15.75	
D1		1.27		
E	10		10.40	
е	2.40		2.70	
e1	4.95		5.15	
F	1.23		1.32	
H1	6.20		6.60	
J1	2.40		2.72	
L	13		14	
L1	3.50		3.93	
L20		16.40		
L30		28.90		
ØР	3.75		3.85	
Q	2.65		2.95	







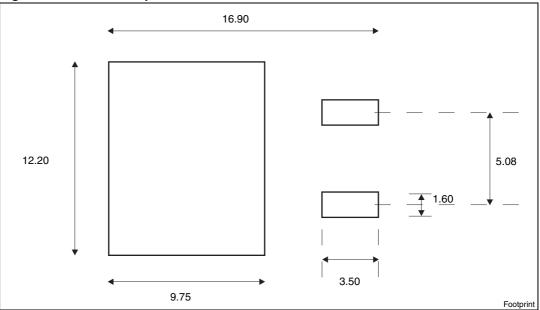


5 Packaging mechanical data

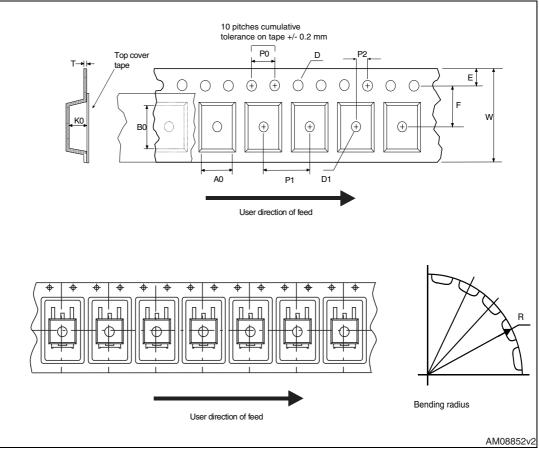
Таре				Reel	
Dim.	mm.		Dim.	mm.	
	Min.	Max.	Dim.	Min.	Max.
A0	10.5	10.7	А		330
B0	15.7	15.9	В	1.5	
D	1.5	1.6	С	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	Т		30.4
P0	3.9	4.1			
P1	11.9	12.1		Base qty	1000
P2	1.9	2.1		Bulk qty	1000
R	50				·
Т	0.25	0.35			
W	23.7	24.3			

Table 10. D²PAK (TO-263) tape and reel mechanical data

Figure 21. D²PAK footprint ^(a)



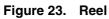


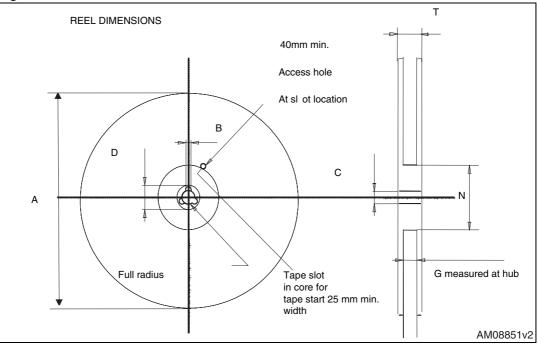


a. All dimension are in millimeters.











6 Revision history

Table 11.	Document revision history
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Date	Revision	Changes
10-Nov-2004	1	New release.
28-Feb-2005	2	Some values changed in Table 4: Static.
16-Dec-2010	3	Updated <i>Table 2: Absolute maximum ratings</i> . Updated mechanical data <i>Section 4: Package mechanical data</i> .
27-Sep-2011	4	Modified: unit value <i>Table 7 on page 5, Figure 2</i> and <i>Figure 3 on page 6.</i> Updated mechanical data D ² PAK <i>Table 8 on page 11</i> and <i>Figure 19 on page 12.</i> Removed order code STGP10NB60SFP and TO-220FP package mechanical data.

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